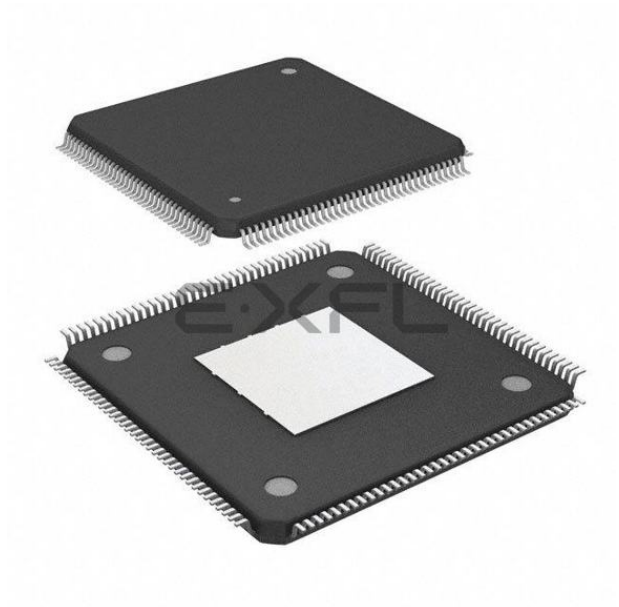

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1000
Number of Logic Elements/Cells	16000
Total RAM Bits	562176
Number of I/O	101
Number of Gates	-
Voltage - Supply	2.85V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LQFP Exposed Pad
Supplier Device Package	144-EQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/10m16sce144c7g

Contents

Operating Conditions

Intel MAX 10 devices are rated according to a set of defined parameters. To maintain the highest possible performance and reliability of the Intel MAX 10 devices, you must consider the operating requirements described in this section.

Absolute Maximum Ratings

This section defines the maximum operating conditions for Intel MAX 10 devices. The values are based on experiments conducted with the devices and theoretical modeling of breakdown and damage mechanisms. The functional operation of the device is not implied for these conditions.

Caution: Conditions outside the range listed in the absolute maximum ratings tables may cause permanent damage to the device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse effects on the device.

Single Supply Devices Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings for Intel MAX 10 Single Supply Devices

Symbol	Parameter	Min	Max	Unit
V_{CC_ONE}	Supply voltage for core and periphery through on-die voltage regulator	–0.5	3.9	V
V_{CCIO}	Supply voltage for input and output buffers	–0.5	3.9	V
V_{CCA}	Supply voltage for phase-locked loop (PLL) regulator and analog-to-digital converter (ADC) block (analog)	–0.5	3.9	V

Dual Supply Devices Absolute Maximum Ratings

Table 3. Absolute Maximum Ratings for Intel MAX 10 Dual Supply Devices

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply voltage for core and periphery	–0.5	1.63	V
V_{CCIO}	Supply voltage for input and output buffers	–0.5	3.9	V
V_{CCA}	Supply voltage for PLL regulator (analog)	–0.5	3.41	V

continued...

Recommended Operating Conditions

Table 8. Recommended Operating Conditions for Intel MAX 10 Devices

Symbol	Parameter	Condition	Min	Max	Unit
V_I	DC input voltage	—	–0.5	3.6	V
V_O	Output voltage for I/O pins	—	0	V_{CCIO}	V
T_J	Operating junction temperature	Commercial	0	85	°C
		Industrial	–40(6)	100	°C
		Automotive	–40(6)	125	°C
t_{RAMP}	Power supply ramp time	—	(7)	10	ms
I_{Diode}	Magnitude of DC current across PCI* clamp diode when enabled	—	—	10	mA

Programming/Erasure Specifications

Table 9. Programming/Erasure Specifications for Intel MAX 10 Devices

This table shows the programming cycles and data retention duration of the user flash memory (UFM) and configuration flash memory (CFM) blocks.

For more information about data retention duration with 10,000 programming cycles for automotive temperature devices, contact your Intel quality representative.

Erase and reprogram cycles (E/P) (8) (Cycles/page)	Temperature (°C)	Data retention duration (Years)
10,000	85	20
10,000	100	10

(6) –40°C is only applicable to Start of Test, when the device is powered-on. The device does not stay at the minimum junction temperature for a long time.

(7) There is no absolute minimum value for the ramp time requirement. Intel characterized the minimum ramp time at 200 µs.

(8) The number of E/P cycles applies to the smallest possible flash block that can be erased or programmed in each Intel MAX 10 device. Each Intel MAX 10 device has multiple flash pages per device.

- Subscript x refers to both V and T.
- ΔR_V is variation of resistance with voltage.
- ΔR_T is variation of resistance with temperature.
- dR/dT is the change percentage of resistance with temperature after calibration at device power-up.
- dR/dV is the change percentage of resistance with voltage after calibration at device power-up.
- V_1 is the initial voltage.
- V_2 is final voltage.

The following figure shows the example to calculate the change of 50 Ω I/O impedance from 25°C at 3.0 V to 85°C at 3.15 V.

Figure 2. Example for OCT Resistance Calculation after Calibration at Device Power-Up

$$\Delta R_V = (3.15 - 3) \times 1000 \times -0.027 = -4.05$$

$$\Delta R_T = (85 - 25) \times 0.25 = 15$$

Because ΔR_V is negative,

$$MF_V = 1/(4.05/100 + 1) = 0.961$$

Because ΔR_T is positive,

$$MF_T = 15/100 + 1 = 1.15$$

$$MF = 0.961 \times 1.15 = 1.105$$

$$R_{final} = 50 \times 1.105 = 55.25\Omega$$

Table 17. Internal Weak Pull-Up Resistor for Intel MAX 10 Devices

Pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO}.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$R_{\_PU}$	Value of I/O pin (dedicated and dual-purpose) pull-up resistor before and during configuration, as well as user mode if the programmable pull-up resistor option is enabled	V_{CCIO} = 3.3 V ± 5%	7	12	34	kΩ
		V_{CCIO} = 3.0 V ± 5%	8	13	37	kΩ
		V_{CCIO} = 2.5 V ± 5%	10	15	46	kΩ
		V_{CCIO} = 1.8 V ± 5%	16	25	75	kΩ
		V_{CCIO} = 1.5 V ± 5%	20	36	106	kΩ
		V_{CCIO} = 1.2 V ± 5%	33	82	179	kΩ

Hot-Socketing Specifications

Table 18. Hot-Socketing Specifications for Intel MAX 10 Devices

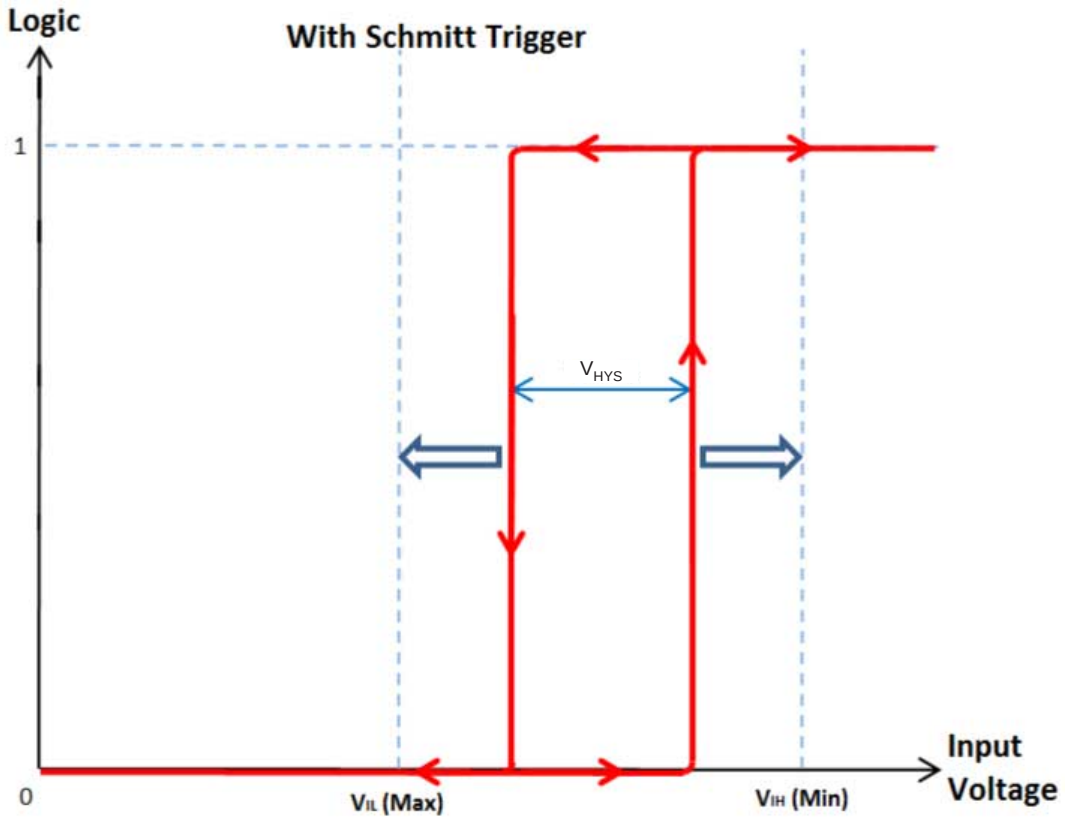
Symbol	Parameter	Maximum
$I_{IOPIN(DC)}$	DC current per I/O pin	300 µA
$I_{IOPIN(AC)}$	AC current per I/O pin	8 mA (13)

Hysteresis Specifications for Schmitt Trigger Input

Intel MAX 10 devices support Schmitt trigger input on all I/O pins. A Schmitt trigger feature introduces hysteresis to the input signal for improved noise immunity, especially for signal with slow edge rate.

(13) The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, $|I_{IOPIN}|$ = C dv/dt, in which C is I/O pin capacitance and dv/dt is the slew rate.

Figure 4. Schmitt Trigger Input Standard Voltage Diagram



I/O Standards Specifications

Tables in this section list input voltage (V_{IH} and V_{IL}), output voltage (V_{OH} and V_{OL}), and current drive characteristics (I_{OH} and I_{OL}) for various I/O standards supported by Intel MAX 10 devices.

For minimum voltage values, use the minimum V_{CCIO} values. For maximum voltage values, use the maximum V_{CCIO} values.

You must perform timing closure analysis to determine the maximum achievable frequency for general purpose I/O standards.

Table 24. Differential HSTL and HSUL I/O Standards Specifications for Intel MAX 10 Devices

I/O Standard	V_{CCIO} (V)			$V_{DIF(DC)}$ (V)		$V_{X(AC)}$ (V)			$V_{CM(DC)}$ (V)			$V_{DIF(AC)}$ (V)
	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max	Min
HSTL-18 Class I, II	1.71	1.8	1.89	0.2	—	0.85	—	0.95	0.85	—	0.95	0.4
HSTL-15 Class I, II	1.425	1.5	1.575	0.2	—	0.71	—	0.79	0.71	—	0.79	0.4
HSTL-12 Class I, II	1.14	1.2	1.26	0.16	V_{CCIO}	0.48 × V_{CCIO}	0.5 × V_{CCIO}	0.52 × V_{CCIO}	0.48 × V_{CCIO}	0.5 × V_{CCIO}	0.52 × V_{CCIO}	0.3
HSUL-12	1.14	1.2	1.3	0.26	—	0.5 × V_{CCIO} – 0.12	0.5 × V_{CCIO}	0.5 × V_{CCIO} + 0.12	0.4 × V_{CCIO}	0.5 × V_{CCIO}	0.6 × V_{CCIO}	0.44

Differential I/O Standards Specifications

Table 25. Differential I/O Standards Specifications for Intel MAX 10 Devices

I/O Standard	V_{CCIO} (V)			V_{ID} (mV)		V_{ICM} (V) (18)			V_{OD} (mV) (19)(20)			V_{OS} (V) (19)		
	Min	Typ	Max	Min	Max	Min	Condition	Max	Min	Typ	Max	Min	Typ	Max
LVPECL (21)	2.375	2.5	2.625	100	—	0.05	D_{MAX} ≤ 500 Mbps	1.8	—	—	—	—	—	—
						0.55	500 Mbps ≤ D_{MAX} ≤ 700 Mbps	1.8						
						1.05	D_{MAX} > 700 Mbps	1.55						
LVDS	2.375	2.5	2.625	100	—	0.05	D_{MAX} ≤ 500 Mbps	1.8	247	—	600	1.125	1.25	1.375
						0.55	500 Mbps ≤ D_{MAX} ≤ 700 Mbps	1.8						

continued...

(18) V_{IN} range: 0 V ≤ V_{IN} ≤ 1.85 V.

(19) R_L range: 90 ≤ R_L ≤ 110 Ω.

(20) Low V_{OD} setting is only supported for RSDS standard.

(21) LVPECL input standard is only supported at clock input. Output standard is not supported.

I/O Standard	V_{CCIO} (V)			V_{ID} (mV)		V_{ICM} (V) (18)			V_{OD} (mV) (19)(20)			V_{OS} (V) (19)		
	Min	Typ	Max	Min	Max	Min	Condition	Max	Min	Typ	Max	Min	Typ	Max
HiSpi	2.375	2.5	2.625	100	—	0.05	D_{MAX} ≤ 500 Mbps	1.8	—	—	—	—	—	—
						0.55	500 Mbps ≤ D_{MAX} ≤ 700 Mbps	1.8						
						1.05	D_{MAX} > 700 Mbps	1.55						

Related Information

Intel MAX 10 LVDS SERDES I/O Standards Support, Intel MAX 10 High-Speed LVDS I/O User Guide
Provides the list of I/O standards supported in single supply and dual supply devices.

Switching Characteristics

This section provides the performance characteristics of Intel MAX 10 core and periphery blocks.

(18) V_{IN} range: 0 V ≤ V_{IN} ≤ 1.85 V.
(19) R_L range: 90 ≤ R_L ≤ 110 Ω.
(20) Low V_{OD} setting is only supported for RSDS standard.

(22) No fixed V_{IN} , V_{OD} , and V_{OS} specifications for Bus LVDS (BLVDS). They are dependent on the system topology.

(23) Mini-LVDS, RSDS, and Point-to-Point Differential Signaling (PPDS) standards are only supported at the output pins for Intel MAX 10 devices.

(24) Supported with requirement of an external level shift

(25) Sub-LVDS input buffer is using 2.5 V differential buffer.

(26) Differential output depends on the values of the external termination resistors.

(27) Differential output offset voltage depends on the values of the external termination resistors.

Embedded Multiplier Specifications

Table 30. Embedded Multiplier Specifications for Intel MAX 10 Devices

Mode	Number of Multipliers	Power Supply Mode	Performance			Unit
			–I6	–A6, –C7, –I7, –A7	–C8	
9 × 9-bit multiplier	1	Single supply mode	198	183	160	MHz
		Dual supply mode	310	260	210	MHz
18 × 18-bit multiplier	1	Single supply mode	198	183	160	MHz
		Dual supply mode	265	240	190	MHz

Memory Block Performance Specifications

Table 31. Memory Block Performance Specifications for Intel MAX 10 Devices

Memory	Mode	Resources Used		Power Supply Mode	Performance			Unit
		LEs	M9K Memory		–I6	–A6, –C7, –I7, –A7	–C8	
M9K Block	FIFO 256 × 36	47	1	Single supply mode	232	219	204	MHz
				Dual supply mode	330	300	250	MHz
	Single-port 256 × 36	0	1	Single supply mode	232	219	204	MHz
				Dual supply mode	330	300	250	MHz
	Simple dual-port 256 × 36 CLK	0	1	Single supply mode	232	219	204	MHz
				Dual supply mode	330	300	250	MHz
	True dual port 512 × 18 single CLK	0	1	Single supply mode	232	219	204	MHz
				Dual supply mode	330	300	250	MHz

Dual Supply Devices ADC Performance Specifications

Table 35. ADC Performance Specifications for Intel MAX 10 Dual Supply Devices

Parameter		Symbol	Condition	Min	Typ	Max	Unit
ADC resolution		—	—	—	—	12	bits
Analog supply voltage		V_{CCA_ADC}	—	2.375	2.5	2.625	V
Digital supply voltage		V_{CCINT}	—	1.15	1.2	1.25	V
External reference voltage		V_{REF}	—	V_{CCA_ADC} – 0.5	—	V_{CCA_ADC}	V
Sampling rate		F_S	Accumulative sampling rate	—	—	1	MSPS
Operating junction temperature range		T_J	—	–40	25	125	°C
Analog input voltage		V_{IN}	Prescalar disabled	0	—	V_{REF}	V
			Prescalar enabled (42)	0	—	3	V
Analog supply current (DC)		I_{ACC_ADC}	Average current	—	275	450	µA
Digital supply current (DC)		I_{CCINT}	Average current	—	65	150	µA
Input resistance		R_{IN}	—	—	(43)	—	—
Input capacitance		C_{IN}	—	—	(43)	—	—
DC Accuracy	Offset error and drift	E_{offset}	Prescalar disabled	–0.2	—	0.2	%FS
			Prescalar enabled	–0.5	—	0.5	%FS
	Gain error and drift	E_{gain}	Prescalar disabled	–0.5	—	0.5	%FS
			Prescalar enabled	–0.75	—	0.75	%FS
	Differential non linearity	DNL	External V_{REF}, no missing code	–0.9	—	0.9	LSB

continued...

(42) Prescalar function divides the analog input voltage by half. The analog input handles up to 3 V input for the Intel MAX 10 dual supply devices.

(43) Download the SPICE models for simulation.

Parameter		Symbol	Condition	Min	Typ	Max	Unit
Conversion Rate [52]	Conversion time	—	Single measurement	—	—	1	Cycle
			Continuous measurement	—	—	1	Cycle
			Temperature measurement	—	—	1	Cycle

Related Information

SPICE Models for Intel FPGAs

Periphery Performance Specifications

This section describes the periphery performance, high-speed I/O, and external memory interface.

Actual achievable frequency depends on design and system specific factors. Ensure proper timing closure in your design and perform HSPICE/IBIS simulations based on your specific design and system setup to determine the maximum achievable frequency in your system.

High-Speed I/O Specifications

For more information about the high-speed and low-speed I/O performance pins, refer to the respective device pin-out files.

Related Information

Documentation: Pin-Out Files for Intel FPGAs

[52] For more detailed description, refer to the Timing section in the *Intel MAX 10 Analog-to-Digital Converter User Guide*.

True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications

Table 36. True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices

True **PPDS** transmitter is only supported at bottom I/O banks. Emulated **PPDS** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	155	5	—	155	5	—	155	MHz
		×8	5	—	155	5	—	155	5	—	155	MHz
		×7	5	—	155	5	—	155	5	—	155	MHz
		×4	5	—	155	5	—	155	5	—	155	MHz
		×2	5	—	155	5	—	155	5	—	155	MHz
		×1	5	—	310	5	—	310	5	—	310	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	310	100	—	310	100	—	310	Mbps
		×8	80	—	310	80	—	310	80	—	310	Mbps
		×7	70	—	310	70	—	310	70	—	310	Mbps
		×4	40	—	310	40	—	310	40	—	310	Mbps
		×2	20	—	310	20	—	310	20	—	310	Mbps
		×1	10	—	310	10	—	310	10	—	310	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	150	5	—	150	5	—	150	MHz
		×8	5	—	150	5	—	150	5	—	150	MHz
		×7	5	—	150	5	—	150	5	—	150	MHz
		×4	5	—	150	5	—	150	5	—	150	MHz
		×2	5	—	150	5	—	150	5	—	150	MHz
		×1	5	—	300	5	—	300	5	—	300	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	300	100	—	300	100	—	300	Mbps
		×8	80	—	300	80	—	300	80	—	300	Mbps
		×7	70	—	300	70	—	300	70	—	300	Mbps

continued...

True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications

Single Supply Devices True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications

Table 37. True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices

True **RSDS** transmitter is only supported at bottom I/O banks. Emulated **RSDS** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	50	5	—	50	5	—	50	MHz
		×8	5	—	50	5	—	50	5	—	50	MHz
		×7	5	—	50	5	—	50	5	—	50	MHz
		×4	5	—	50	5	—	50	5	—	50	MHz
		×2	5	—	50	5	—	50	5	—	50	MHz
		×1	5	—	100	5	—	100	5	—	100	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	100	100	—	100	100	—	100	Mbps
		×8	80	—	100	80	—	100	80	—	100	Mbps
		×7	70	—	100	70	—	100	70	—	100	Mbps
		×4	40	—	100	40	—	100	40	—	100	Mbps
		×2	20	—	100	20	—	100	20	—	100	Mbps
		×1	10	—	100	10	—	100	10	—	100	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	50	5	—	50	5	—	50	MHz
		×8	5	—	50	5	—	50	5	—	50	MHz
		×7	5	—	50	5	—	50	5	—	50	MHz
		×4	5	—	50	5	—	50	5	—	50	MHz
		×2	5	—	50	5	—	50	5	—	50	MHz
		×1	5	—	100	5	—	100	5	—	100	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	100	100	—	100	100	—	100	Mbps

continued...

Emulated RSDS_E_1R Transmitter Timing Specifications

Table 39. Emulated RSDS_E_1R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices

Emulated **RSDS_E_1R** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	85	5	—	85	5	—	85	MHz
		×8	5	—	85	5	—	85	5	—	85	MHz
		×7	5	—	85	5	—	85	5	—	85	MHz
		×4	5	—	85	5	—	85	5	—	85	MHz
		×2	5	—	85	5	—	85	5	—	85	MHz
		×1	5	—	170	5	—	170	5	—	170	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	170	100	—	170	100	—	170	Mbps
		×8	80	—	170	80	—	170	80	—	170	Mbps
		×7	70	—	170	70	—	170	70	—	170	Mbps
		×4	40	—	170	40	—	170	40	—	170	Mbps
		×2	20	—	170	20	—	170	20	—	170	Mbps
		×1	10	—	170	10	—	170	10	—	170	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	85	5	—	85	5	—	85	MHz
		×8	5	—	85	5	—	85	5	—	85	MHz
		×7	5	—	85	5	—	85	5	—	85	MHz
		×4	5	—	85	5	—	85	5	—	85	MHz
		×2	5	—	85	5	—	85	5	—	85	MHz
		×1	5	—	170	5	—	170	5	—	170	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	170	100	—	170	100	—	170	Mbps
		×8	80	—	170	80	—	170	80	—	170	Mbps
		×7	70	—	170	70	—	170	70	—	170	Mbps

continued...

Symbol	Parameter	Mode	–C7, –I7		–A7		–C8		Unit
			Min	Max	Min	Max	Min	Max	
		×8	80	200	80	200	80	200	Mbps
		×7	70	200	70	200	70	200	Mbps
		×4	40	200	40	200	40	200	Mbps
		×2	20	200	20	200	20	200	Mbps
		×1	10	200	10	200	10	200	Mbps
SW	Sampling window (high-speed I/O performance pin)	—	—	910	—	910	—	910	ps
	Sampling window (low-speed I/O performance pin)	—	—	1,110	—	1,110	—	1,110	ps
$t_{x\ Jitter}$(71)	Input jitter	—	—	1,000	—	1,000	—	1,000	ps
t_{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	—	—	1	—	1	—	1	ms

Dual Supply Devices LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications

Table 46. LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications for Intel MAX 10 Dual Supply Devices

LVDS, **TMDS**, **HiSpi**, **SLVS**, and **Sub-LVDS** receivers are supported at all banks.

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7		–A7		–C8		Unit
			Min	Max	Min	Max	Min	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	350	5	320	5	320	MHz
		×8	5	360	5	320	5	320	MHz
		×7	5	350	5	320	5	320	MHz
		×4	5	360	5	320	5	320	MHz

continued...

(71) TX jitter is the jitter induced from core noise and I/O switching noise.

Memory Output Clock Jitter Specifications

Intel MAX 10 devices support external memory interfaces up to 303 MHz. The external memory interfaces for Intel MAX 10 devices calibrate automatically.

The memory output clock jitter measurements are for 200 consecutive clock cycles.

The clock jitter specification applies to memory output clock pins generated using DDIO circuits clocked by a PLL output routed on a PHY clock network.

DDR3 and LPDDR2 SDRAM memory interfaces are only supported on the fast speed grade device.

Table 48. Memory Output Clock Jitter Specifications for Intel MAX 10 Devices

Parameter	Symbol	–6 Speed Grade		–7 Speed Grade		Unit
		Min	Max	Min	Max	
Clock period jitter	$t_{JIT(per)}$	–127	127	–215	215	ps
Cycle-to-cycle period jitter	$t_{JIT(cc)}$	—	242	—	360	ps

Related Information

Literature: External Memory Interfaces
Provides more information about external memory system performance specifications, board design guidelines, timing analysis, simulation, and debugging information.

Configuration Specifications

This section provides configuration specifications and timing for Intel MAX 10 devices.

Device	CFM Data Size (bits)	
	Without Memory Initialization	With Memory Initialization
10M25	4,140,000	4,780,000
10M40	7,840,000	9,670,000
10M50	7,840,000	9,670,000

Internal Configuration Time

The internal configuration time measurement is from the rising edge of nSTATUS signal to the rising edge of CONF_DONE signal.

Table 53. Internal Configuration Time for Intel MAX 10 Devices (Uncompressed .rbf)

Device	Internal Configuration Time (ms)							
	Unencrypted				Encrypted			
	Without Memory Initialization		With Memory Initialization		Without Memory Initialization		With Memory Initialization	
	Min	Max	Min	Max	Min	Max	Min	Max
10M02	0.3	1.7	—	—	1.7	5.4	—	—
10M04	0.6	2.7	1.0	3.4	5.0	15.0	6.8	19.6
10M08	0.6	2.7	1.0	3.4	5.0	15.0	6.8	19.6
10M16	1.1	3.7	1.4	4.5	9.3	25.3	11.7	31.5
10M25	1.0	3.7	1.3	4.4	14.0	38.1	16.9	45.7
10M40	2.6	6.9	3.2	9.8	41.5	112.1	51.7	139.6
10M50	2.6	6.9	3.2	9.8	41.5	112.1	51.7	139.6

Table 54. Internal Configuration Time for Intel MAX 10 Devices (Compressed .rbf)

Compression ratio depends on design complexity. The minimum value is based on the best case (25% of original `.rbf` sizes) and the maximum value is based on the typical case (70% of original `.rbf` sizes).

Device	Internal Configuration Time (ms)			
	Unencrypted/Encrypted			
	Without Memory Initialization		With Memory Initialization	
	Min	Max	Min	Max
10M02	0.3	5.2	—	—
10M04	0.6	10.7	1.0	13.9
10M08	0.6	10.7	1.0	13.9
10M16	1.1	17.9	1.4	22.3
10M25	1.1	26.9	1.4	32.2
10M40	2.6	66.1	3.2	82.2
10M50	2.6	66.1	3.2	82.2

Internal Configuration Timing Parameter

Table 55. Internal Configuration Timing Parameter for Intel MAX 10 Devices

Symbol	Parameter	Device	Minimum	Maximum	Unit
t_{CD2UM}	`CONF_DONE` high to user mode	10M02, 10M04, 10M08, 10M16, 10M25	182.8	385.5	µs
		10M40, 10M50	275.3	605.7	µs

I/O Timing

The data is typically used prior to designing the FPGA to get an estimate of the timing budget as part of the link timing analysis.

The Intel Quartus Prime Timing Analyzer provides a more accurate and precise I/O timing data based on the specific device and design after you complete place-and-route.

Date	Version	Changes
May 2015	2015.05.04	• Updated a note to V_{CCIO} for both single supply and dual supply power supplies recommended operating conditions tables. Note updated: V_{CCIO} for all I/O banks must be powered up during user mode because V_{CCIO} I/O banks are used for the ADC and I/O functionalities. • Updated Example for OCT Resistance Calculation after Calibration at Device Power-Up. • Removed a note to BLVDS in Differential I/O Standards Specifications for Intel MAX 10 Devices table. BLVDS is now supported in Intel MAX 10 single supply devices. Note removed: BLVDS TX is not supported in single supply devices. • Updated ADC Performance Specifications for both single supply and dual supply devices. — Changed the symbol for Operating junction temperature range parameter from T_A to T_J. — Edited sampling rate maximum value from 1000 kSPS to 1 MSPS. — Added a note to analog input voltage parameter. — Removed input frequency, f_{IN} specification. — Updated the condition for DNL specification: External V_{REF}, no missing code. Added DNL specification for condition: Internal V_{REF}, no missing code. — Added notes to AC accuracy specifications that the value with prescalar enabled is 6dB less than the specification. — Added a note to On-Chip Temperature Sensor (absolute accuracy) parameter about the averaging calculation. • Updated ADC Performance Specifications for Intel MAX 10 Single Supply Devices table. — Added condition for On-Chip Temperature Sensor (absolute accuracy) parameter: with 64 samples averaging. • Updated ADC Performance Specifications for Intel MAX 10 Dual Supply Devices table. — Updated Digital Supply Voltage minimum value from 1.14 V to 1.15 V and maximum value from 1.26 V to 1.25 V. • Updated f_{HSCLK} and HSIODR specifications for –A7 speed grade in the following tables: — True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True LVDS Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices — True LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices — Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — LVDS Receiver Timing Specifications for Intel MAX 10 Single Supply Devices — LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications for Intel MAX 10 Dual Supply Devices

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Date	Version	Changes
		• Updated TCCS specifications in the following tables: — True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated RSDS_E_1R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True LVDS Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices — True LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices — Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices • Updated $t_{x\ Jitter}$ specifications in the following tables: — True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated RSDS_E_1R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices • Updated SW specifications in LVDS Receiver Timing Specifications for Intel MAX 10 Single Supply Devices table. • Added a note to $t_{x\ Jitter}$ for all LVDS tables. Note: TX jitter is the jitter induced from core noise and I/O switching noise. • Updated the description for t_{LOCK} for all LVDS tables: Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration. • Updated Memory Output Clock Jitter Specifications section. — Updated maximum external memory interfaces frequency from 300 MHz to 303 MHz. — Updated PLL output routing from global clock network to PHY clock network. • Added I/O Timing for Intel MAX 10 Devices table. • Added V_{HYS} in the Glossary table.
January 2015	2015.01.23	• Removed a note to V_{CCA} in Power Supplies Recommended Operating Conditions for Intel MAX 10 Dual Supply Devices table. This note is not valid: All V_{CCA} pins must be connected together for EQFP package. • Corrected the maximum value for $t_{OUTJITTER\_CCJ\_IO}$ ($F_{OUT} \geq 100$ MHz) from 60 ps to 650 ps in PLL Specifications for Intel MAX 10 Devices table.
December 2014	2014.12.15	• Restructured Programming/Erasure Specifications for Intel MAX 10 Devices table to add temperature specifications that affect the data retention duration. • Added statements in the I/O Pin Leakage Current section: Input channel leakage of ADC I/O pins due to hot socket is up to maximum of 1.8 mA. The input channel leakage occurs when the ADC IP core is enabled or disabled. This is applicable to all Intel MAX 10 devices with ADC IP core, which are 10M04, 10M08, 10M16, 10M25, 10M40, and 10M50 devices. The ADC I/O pins are in Bank 1A. • Added a statement in the I/O Standards Specifications section: You must perform timing closure analysis to determine the maximum achievable frequency for general purpose I/O standards.

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